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► To cite this version:

F. Djeflal, Nacereddine Boubiche, H. Ferhati, Jacques Faerber, François Le Normand, et al.. Highly efficient and low-cost multispectral photodetector based on RF sputtered a-Si/Ti multilayer structure for Si-photonics applications. *Journal of Alloys and Compounds*, 2021, 876, 10.1016/j.jallcom.2021.160176 . hal-03249129

HAL Id: hal-03249129

<https://hal.science/hal-03249129>

Submitted on 29 Sep 2021

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Highly efficient and low-cost broadband multispectral photodetector based on RF sputtered a-Si/Ti structure

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Abstract

In this paper, a new cost-effective multispectral photodetector (PD) based on amorphous-silicon (a-Si)/titanium (Ti) structure, which achieves a high UV-Visible-NIR photoresponse is elaborated. A new design strategy based on combining FDTD (Finite Difference Time Domain) with GA (Genetic Algorithm) was used to determinate the a-Si/Ti multilayer geometry providing the highest photoresponsivity in UV, Visible and NIR regions. The optimized structure is then fabricated using RF magnetron sputtering technique. A comprehensive analysis of the photodetector electrical, optical and structural properties was carried out. The sputtered a-Si/Ti multilayer was characterized by Scanning Electron Microscopy (SEM), X-ray diffraction (XRD), and UV-Visible-NIR absorption spectroscopy. The a-Si/Ti multilayer PD exhibits a high broadband absorbance of 80% over the UV and even NIR spectrum ranges [200nm-1100nm]. Moreover, photoelectrical characterization showed that the developed device exhibits an improved responsivity under UV, Visible and NIR lights (1.9 A/W at 365nm, 1.24 A/W at 550 nm and 0.93 A/W at 900 nm) and a high I_{ON}/I_{OFF} ratio of 68 dB. The broadband multispectral photodetection property offered by the proposed a-Si/Ti multilayer PD opens a new route for the fabrication of promising alternative photodetectors for future high-performance and cost-effective optoelectronic systems.

Key words: broadband; RF sputtering; multispectral; photodetector; a-Si/Ti.

1. Introduction

Optoelectronic systems based on the Silicon-photonics platform are predicted to be the most practical technology to meet the cost-effective, large bandwidth, and low power consumption requirements [1-4]. Photodetectors (PDs), which are the key components of optoelectronic communication systems, have received an important research interest due to their large applications in biomedical imaging, optical wireless communication, light-detection and robotics [4-8]. Several published works have developed new PD devices, which can detect different wavelength bands ranging from UV to infrared by using adequate semiconductor photosensitive materials with appropriate band-gap values [7-10]. Moreover, the PDs can become more efficient in extensive applications when they are able to detect the broadband multispectral radiations (UV-Visible-NIR) [10-12]. However, the development of multispectral and broadband PDs mainly depends on the control and selection of the suitably matched band-gap materials in order to cover the multispectral range, which is regarded quite challenging. Several works have been proposed to overcome this challenge suggested developing alternative materials and device structures for broadband multispectral photosensing applications. In this context, new design methodologies and structures including plasmonic nanoparticles, core-shell nanostructures, nanowires, metal oxides-based heterojunction and quantum dots have been developed to achieve high broadband absorbance characteristics [10-20]. Despite the capability of these designs to provide the broadband multispectral photodetection, they require costly fabrication techniques and high thermal budget. Additionally, the interface defects associated with different heterostructure materials can affect the carrier transport efficiency and light trapping mechanism, thus limiting the sensor photoresponsivity. In this context, researchers have turned out their focus towards the use of 2D-materials and mono-layers in order to overcome these limitations. This is mainly due to their broadband absorption capability, flexibility and high electron mobility [21-23].

Nevertheless, PDs based on 2D-materials reveal a low responsivity due to severe charge recombination effects and its weak absorption behavior. Therefore, the development of novel efficient and low-cost broadband multispectral photodetectors is required to improve the capabilities of optoelectronic technology. Motivated by this concept, the present work aims at developing a new low-cost and highly efficient multispectral photodetector based on RF sputtered a-Si/Ti multilayer structure for Si-phonic applications. To the best of our knowledge, no design techniques based on experiments assisted by numerical optimization using FDTD and GA computations were conducted to develop broadband multispectral PDs using a-Si/Ti multilayer structure. Accordingly, the optimized a-Si/Ti multilayer structure was prepared using RF magnetron sputtering technique. Structural, optical and electrical characterizations of the elaborated a-Si/Ti-based PD were carried out. It is revealed that the developed PD demonstrates outstanding broadband multispectral absorption capabilities over a wide spectrum range with high electrical performances. Therefore, the proposed approach provides a sound pathway for developing broadband sensors based on simple and low-cost structures for high performance Si-photonics applications.

2. Device design and experiments

The development of Broadband multispectral PDs based on a-Si material is extremely difficult. This constraint is mainly due to the intrinsic limited absorption edge of this material. To overcome this absorption limitation, in this work we investigate a new multispectral PD based on non-hydrogenated a-Si dwells on introducing intermediate Ti ultra-thin layers. In this context, Fig.1 (a) illustrates a cross-sectional view of the investigated a-Si/Ti multilayer-based PD device, where highly transparent ITO thin layer is deposited at the top of the structure to reduce the optical reflection losses [4]. The a-Si/Ti multilayer structure is sputtered considered on a glass substrate. As it is shown in this Figure, $d_{a-Si} = [d_{Si1}, d_{Si2}, \dots, d_{Sin}]$ and $t_{Ti} = [t_{Ti1}, t_{Ti2}, \dots, t_{Tij}]$ represent the thickness vector values

associated with the silicon and titanium layers, respectively. The thickness of the PD device is $t_{a-Si/Ti}$. For the numerical simulation framework, the optical properties (absorbance, reflectance and transmittance) of the investigated PD structure are calculated using FDTD method provided SILVACO software [24].

As far as we are concerned, the development of highly efficient and low-cost multispectral sensors through intuiting the multi-layer structural, geometrical and electrical parameters by using the well-known optical and electrical properties of PDs is not sufficient to achieve the best electrical performances and highest photoresponsivity over a wide spectrum range. Alternatively, we believe that sophisticated numerical optimization strategies behaving like predictive simulations are required to forecast the sensor performance. In this context, the use metaheuristic optimization approaches such as GA technique is a powerful tool for identifying the optimal geometrical configuration of the a-Si/Ti multilayer structure to achieve the highest multispectral photoresponsivity. To do so, Fig.1 (b) shows the flowchart of the adopted hybrid design approach based on combined GA and numerical simulation techniques. The optical device properties are simulated using 2D-FDTD method. More details regarding the suggested modeling approach can be found in our previously published works [25-27].

The simulated spectral absorbance using FDTD technique is explored to formulate the objective (fitness) function, which will be minimized using GA-based optimization method. The fitness function is given by the following formula

$$Fitness (X_i) = \left(\frac{1}{A[\lambda_{min}, \lambda_{max}]} \right) \quad (1)$$

where A represents the average absorbance over the spectral range of $[\lambda_{min}, \lambda_{max}]$ with $\lambda_{min} = 200nm$ and $\lambda_{max} = 1100nm$ are respectively the minimum and the maximum wavelength values considered for broadband photosensing of PDs, X_i denotes the design

parameter vector. Various metals (Ag, Au, Ni and Ti) are introduced in the optimization procedure. After carrying out the optimization procedure, the resulted design parameter vector of the investigated a-Si/Ti multilayer active-film is given by $X_i = (d_{a-Si} = [20nm, 36nm, 50nm, 40nm], t_{ITO} = 20nm, t_{Ti} = [9nm, 8nm, 7nm], j = 3)$. While the optimized metal is the Titanium, the optimized PD structure reveals a very high average absorbance of 83.6% over UV-Vis-NIR spectral range, indicating its broadband sensing properties. This makes it a promising candidate for elaborating highly efficient and low-cost multispectral photodetectors. This enhancement is attributed to the role of GA-based optimization tool in selecting the appropriate multilayer structure through promoting enhanced light-scattering effects. The obtained design will be used to elaborate the optimized a-Si/Ti multilayer sensor, which is the main objective of the next part.

The elaboration of the optimized PD is based on three-step manufacturing processes. In the beginning, glass substrates were ultrasonically cleaned up using an ultrasonic bath and commercial detergent and then dried under a nitrogen jet procedure. Afterwards, successive deposition of the optimized a-Si and Ti thin-films on the glass substrate was carried out using *RF* magnetron sputtering technique (MOORFIELD MiniLab 060). To do so, p-type Si and Ti targets with high purity of 99.99% were used. This experimental technique is commonly used to elaborate high-quality thin-layers [28-30]. The sputtering process was performed in a pure *Ar* atmosphere with a pressure of 1.5 Pa. The deposition parameters were carefully tuned in order to obtain unhydrogenated a-Si state, Besides, the targets to substrate distances were kept at 6.5 cm and 5.1 cm for the Titanium and Si materials, respectively. The sputtering deposition parameters for all sub-layers are summarized in Table.1. The ITO ultrathin film was deposited on the sputtered a-Si/Ti multilayer by using targets with 90 wt% In_2O_3 and 10 wt% SnO_2 . It is worthy to note that the RF sputter was calibrated before the deposition of

deferent thin films, where each layer was separately grown on glass substrates to select the appropriate deposition parameters.

In order to assess the optoelectronic performances of the fabricated sensor, structural and optical characterizations were conducted using X-ray diffraction measurements (ARL Equinox 3000) for 2θ diffraction angle scans of $[25^\circ-80^\circ]$ and UV-Visible-NIR spectrophotometer (F10-RT-UV). The morphological characteristics of the prepared sample were analyzed using scanning electron microscopy (SEM), where the surface (top) was imaged with a Zeiss Gemini SEM 500 with a field emission Schottky source. The semiconductor characterization system (Keithley 4200-SCS) was employed to measure the current-voltage characteristics of the prepared device under dark and illumination conditions.

3. Results and discussions

The aim of this work is to investigate the role of introducing a-Si/Ti multilayered structure with optimized geometry in improving the photosensing performances of PDs over a wide spectral range. The structural properties of the prepared sample based on embedded a-Si and Ti sputter-deposited thin-films are investigated using XRD technique. In this context, Fig.2 (a) shows XRD measurements for (2θ) diffraction angle scanning from 25° to 80° of the prepared samples based on ITO/a-Si thin-film and a-Si/Ti multilayered structure. The XRD pattern of the elaborated sample with ITO/a-Si shows a low-intensity XRD peak indexed to the (222) crystal plane of the ITO material. It can be also seen from this spectra the presence of a diffraction peak at 28.5° angle, corresponding the (111) facets of silicon. This indicates that the sputtering of thick Si films ($t_{a-Si}=130$ nm) enables the formation of Si microcrystals. However, it can be noticed from the XRD pattern of the elaborated a-Si/Ti multilayer structure depicted in Fig.2 (a), the amorphous state of the silicon and ITO sputtered layers, where no coherent XRD peaks are matching these materials. The obtained crystalline characteristics can be explained by the ultralow thickness of the deposited silicon sub-layers,

which can prevent reaching the crystallization phase of the Si material. On the other hand, this pattern demonstrates the presence of crystallized Ti metal, manifesting (101)-oriented film at the diffraction angle of 39.5° . This highlights the beginning of the crystallization phase of the deposited Ti inter-layers. Fig.2 (b) shows the SEM top surface image of the fabricated ITO/a-Si/Ti multilayered sample. It can be seen from this micrograph that granulated ITO surface with roughness characteristics is observed. This indicates that the growth is essentially columnar for the embedded a-Si and Ti sub-layers, which further explains the obtained amorphous state of the sputtered silicon thin-films as it is shown in Fig.2 (a). In other words, as the a-Si and Ti thin-films are embedded by RF sputtering technique, the structure roughness significantly increases and when the grain size is superior to the film thickness, the growth becomes columnar particularly for the deposited layers closest to the surface.

One of the most important criteria that active layers of multispectral PDs should satisfy is to offer a broadband absorption property. To assess the absorption capabilities of the prepared sample based on stacked a-Si and Ti sub-layers with optimized geometry, the absorbance spectra of the elaborated samples were extracted and illustrated in Fig.3. It can be observed from this figure that significant changes concerning the optical behavior of the PD active film are achieved by inserting an optimized a-Si/Ti multilayer. It demonstrates highly improved absorption efficiency exceeding 80% over UV-Vis-NIR spectral range as compared to that of a-Si thin-film (28.2%). This yields a high relative enhancement of 183%. In addition, the obtained experimental results are found in a good agreement with the theoretical ones, thus indicating the accuracy of the exploited numerical modeling technique. This achievement is due to the effectiveness of the introduced FDTD-GA hybrid approach in promoting enhanced light trapping capabilities of embedded a-Si and Ti sub-layers with suitable geometry. In other words, the introduction of Ti intermediate metal films within the a-Si layer can generate optical micro-cavities, which leads to extend the optical path in the PD active layer thereby

resulting in a broadband absorption characteristic. Therefore, the fabrication of such an optimized a-Si/Ti multilayered structure as an MSM photodetector can extend the light harvesting capability into the visible and NIR spectral ranges, making it very promising candidate for the development of high-responsivity broadband PDs at low-cost.

To further investigate the multispectral photoresponse of the prepared PD based on stacked a-Si and Ti thin-films, the sample is realized as an MSM photodetector. In this framework, top and bottom gold contacts were evaporated via E-beam evaporation technique as it is shown in Fig.1 (a). The fabricated device was then illuminated by monochromatic light signals with wavelength values of 365 nm, 550 nm and 900 nm using LED lamps. Consequently, the measured I-V characteristics in darkness and under illumination conditions of the prepared sensors based on a-Si and a-Si/Ti multilayer active films are depicted in Fig.4 (a) and (b) respectively. It can be seen from Fig.4 (a) that the a-Si based PD shows a good photoresponse only in the UV range. On the other hand, Fig.4 (b) demonstrates the ability of the prepared PD with embedded a-Si and Ti sub-layers for providing multispectral photodetection capability. The device shows excellent sensing properties with high photocurrent values of 0.68 mA, 0.22 mA and 0.1 mA under UV, visible and NIR lights, respectively at an applied voltage of 3V. Such finding correlates well with the above-outlined broadband absorption characteristic of the optimized structure based on embedded a-Si and Ti thin-films. Basically, the latter structure shows an extended absorption to the visible and NIR regions, which can enable enhancing the carrier generation mechanism. This effect leads to achieve an improved broadband photoresponse. Moreover, the use of stacked a-Si and Ti layers can enlarge the depletion layer in the active layer due to the Schottky nature of the a-Si/Ti contact. This can in turn improve the separation mechanism of the photo-excited e/h pairs, thus reducing recombination losses. It can be also observed from this figure that the proposed PD based on a-Si/Ti multilayer provides a favorable photocurrent at self-powered

condition, where the measured I-V curves are shifted to negative voltages. This phenomenon is attributed to the degraded homogeneity of the deposited sub-layers, where the sputtering of a-Si and Ti layers closest to the surface is principally columnar as it is above-outlined.

To show the capability of the proposed experiment assisted by FDTD-GA hybrid approach in developing broadband PDs based on simple and low-cost structures, Fig.5 depicts the measured spectral responsivity of the elaborated samples based on a-Si thin-film and stacked a-Si and Ti layers. Clearly, the proposed sensor demonstrates a high responsivity over a large spectral band from UV to NIR as compared to the conventional device. The prepared PD with a-Si/Ti multilayered active film exhibits superior responsivity values of 1.9 A/W, 1.24A/W and 93 mA/W under UV, visible and NIR illumination conditions, respectively. This multispectral photoresponse can be attributed to the role of introducing inter-metallic layer in promoting enhanced antireflection capabilities. Besides, the use of an effective approach based on experiment assisted by combined FDTD-PSO design methodology enables enhancing the photogeneration/collection efficiency.

To show the strength of the prepared multispectral PD based on a simple and low-cost embedded a-Si and Ti thin-films as compared to recently developed ones, a comparative performance analysis is carried out. Accordingly, the associated FoM parameters including current ratio (I_{ON}/I_{OFF} ratio), responsivity and detectivity are extracted and summarized in Table.2. This table confirms the ability of the optimized structure for outperforming other perovskite, silicon and nanostructured multispectral PD structures in terms of FoM parameters [31-40]. Although some reported devices demonstrated superior visible photoresponse, they either exhibited a compromised UV sensitivity, stability issues and/or required the use of critical raw materials and processing complexity. Alternatively, the present PD with stacked a-Si and Ti thin-films provides a new strategy for achieving high and broadband photosensing characteristics at low manufacturing cost. These results clearly demonstrate the great potential

of the proposed a-Si/Ti multilayer structure for multispectral photodetection application.

4. Conclusion

In this work, we have developed a new high-photoresponsivity multispectral PD based on ITO/a-Si multilayer structure. The numerical simulation and optimization of the structure using combined FDTD-GA approach offer improved photoresponsivity and broadband absorption capabilities. The optimized design was employed in fabricating multispectral photodetector using RF magnetron sputtering technique. The device structural and optical properties were investigated using XRD and UV-Vis-NIR spectroscopy methods. It was found that excellent UV-Vis-NIR absorbance with over than 80% average value was recorded which can lead to improve the device photoresponsivity. In this context, the elaborated sensor offers ultra-high responsivity values of 1.9 A/W, 1.24A/W and 0.93 A/W under UV, visible and NIR illumination, respectively. This multispectral photodetection property is mainly attributed to the effective light-management provided by the optimized design. Moreover, it is demonstrated that the elaborated PD based on embedded a-Si and Ti sub-layers can operate in self-powered mode, showing a favorable photocurrent of 0.4 μ A. The proposed elaboration methodology can contribute in a fascinating breakthrough towards broadband multispectral photodetector devices based on Si-photonics platform.

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Figures caption:

Fig.1 (a): Device structure with MSM Schottky PD configuration based on the proposed a-Si/Ti multilayer structure. **(b)** Flowchart of the adopted hybrid design approach based on combined GA and numerical simulation techniques.

Fig.2 (a) X-ray diffraction patterns of the elaborated a-Si/Ti structure with $t_{\text{a-Si/Ti}}=170\text{nm}$ and $t_{\text{ITO}}=20\text{nm}$. **(b)** SEM images of top surface of the elaborated a-Si/Ti multilayer structure using RF magnetron sputtering technique.

Fig.3: Absorbance spectra of the prepared ITO/a-Si and a-Si/Ti multilayer samples with $t_{\text{a-Si/Ti}}=170\text{nm}$ and $t_{\text{ITO}}=20\text{nm}$.

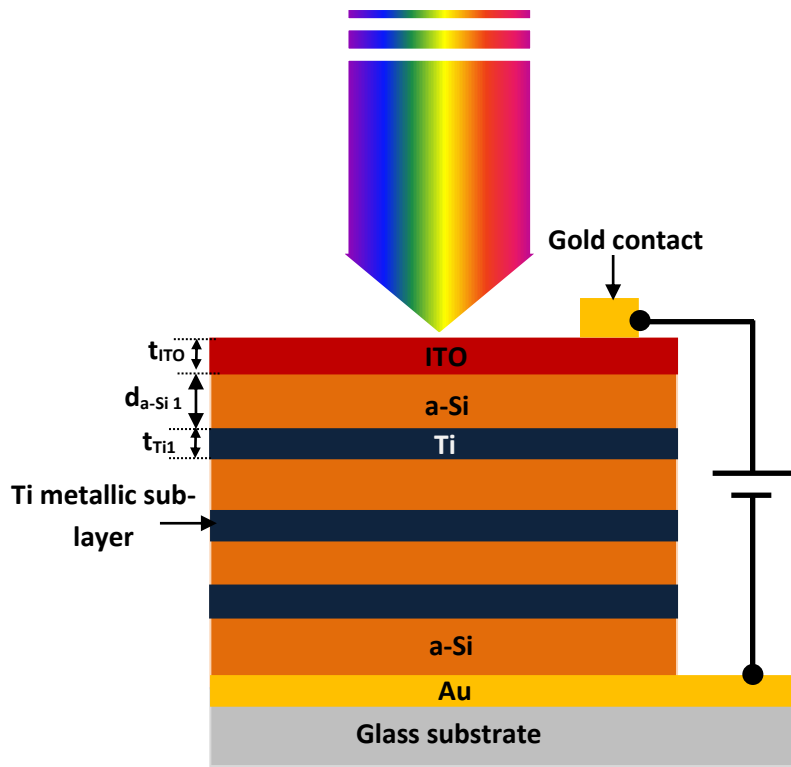
Fig.4: Measured I-V characteristics under dark and light-exposure conditions in UV, visible and NIR spectrum bands of **(a)** the conventional device with a-Si active layer, **(b)** the prepared PD based on embedded a-Si and Ti sub-layers.

Fig.5: Spectral photoresponsivity of the prepared PD structures based on a-Si thin-film and a-Si/Ti multilayer.

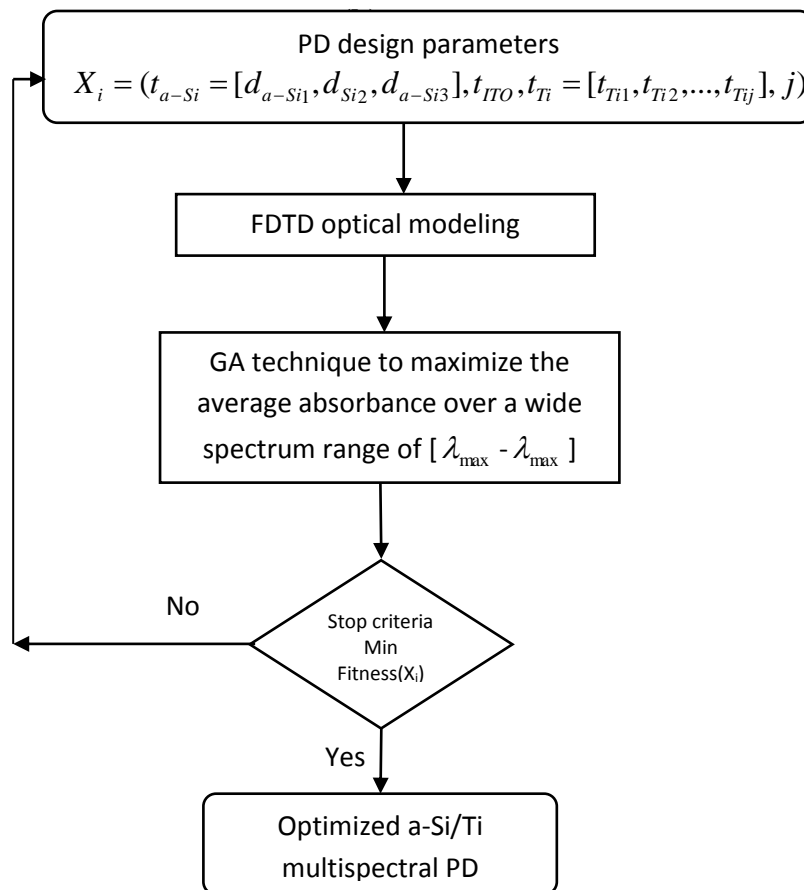
Tables:

Table.1: Deposition parameters of the sputtered ITO/a-Si/Ti multilayer structure.

Table.2: Overall performance comparison between the elaborated PD and several reported multispectral photodetector devices.

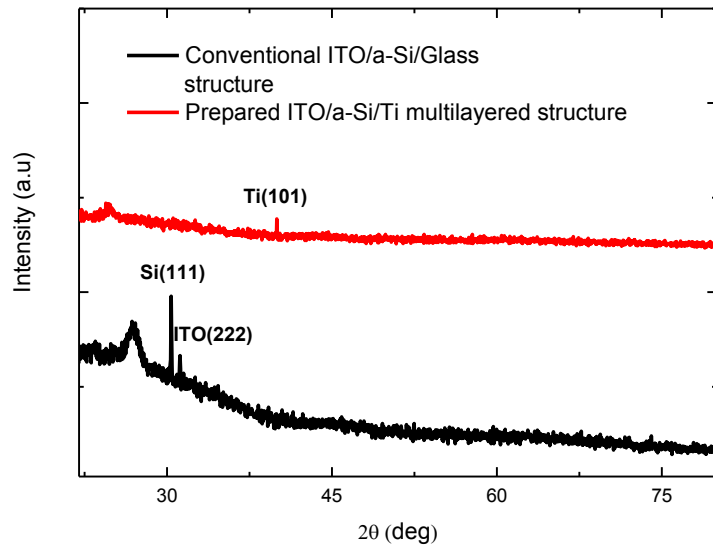


(a)

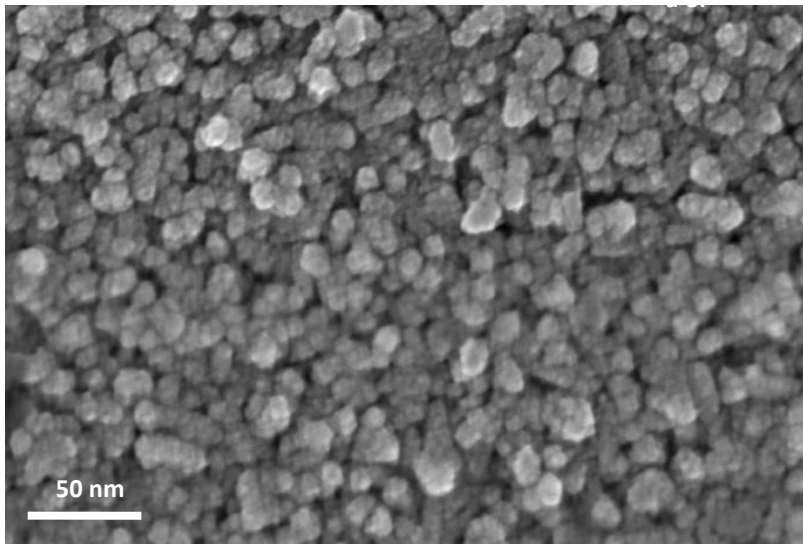


(b)

Figure.1



(a)



(b)

Figure.2

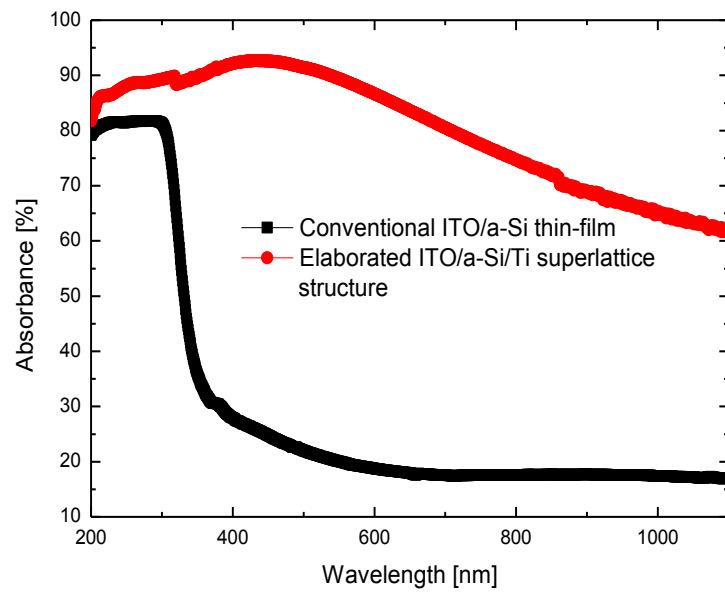
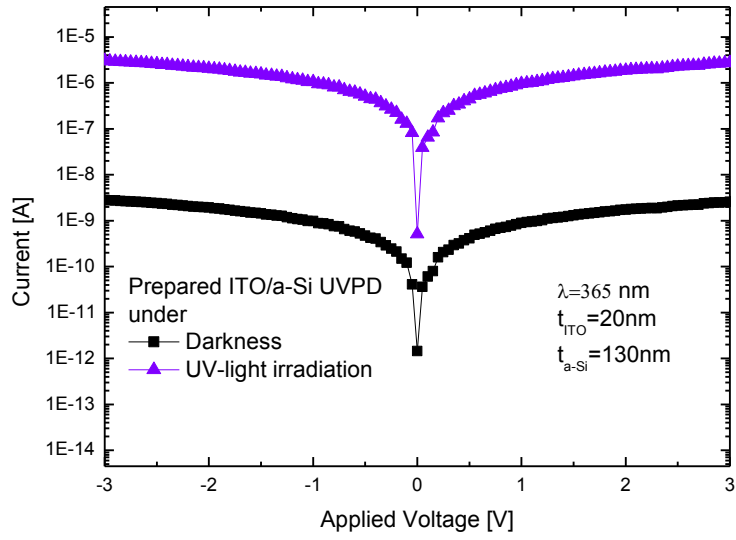
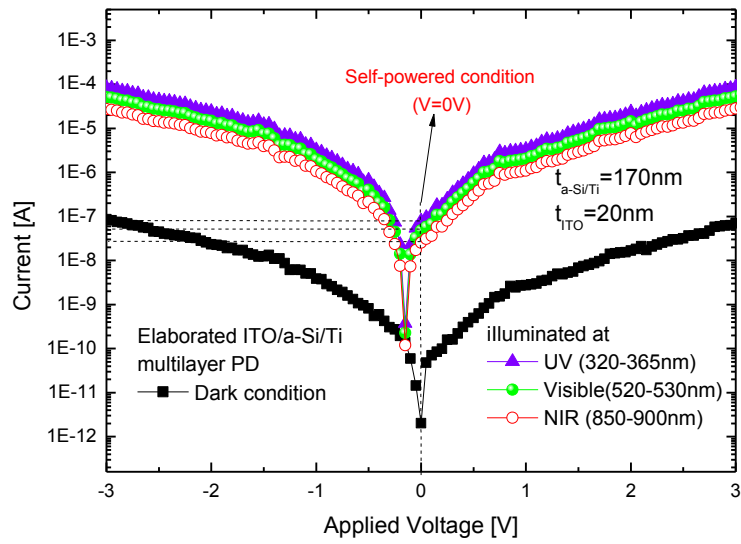


Figure.3



(a)



(b)

Figure.4

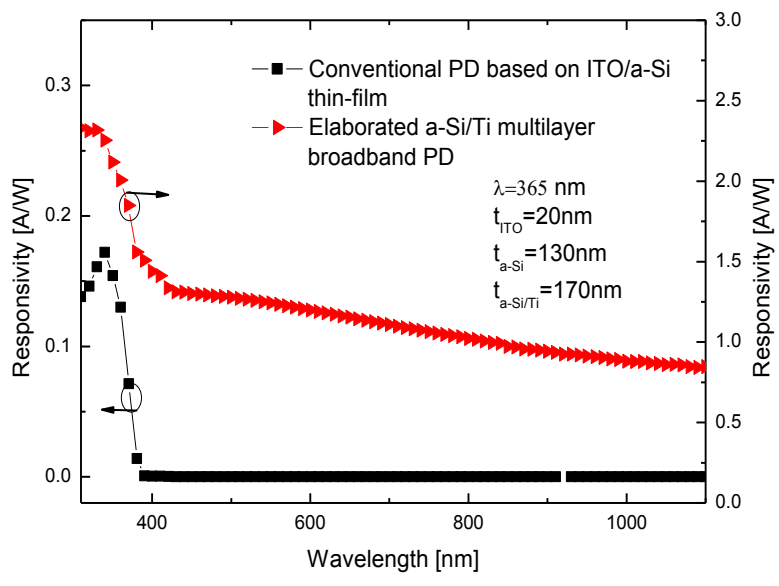


Figure.5

Table.1

Parameter	ITO	a-Si	Ti
Target	(90% In ₂ O ₃ ,10% SnO ₂)	99.99% p-Si	99.99% Ti
Target to substrate distance (cm)	5	5.1	6.5
Gas composition (Ar: O ₂)	(66%: 33%)	/	/
Substrate temperature (K)	300	300	300
power of <i>RF</i> source (W)	240	250	250
Working pressure (Pa)	1.5	1.5	1.5
deposition rate (nm/s)	0.2	0.4	0.7

Table.2

UV-Vis-NIR PD structures	UV (320-365 nm)			Visible (green) (515-525 nm)			NIR (880-900 nm)			Ref.
	I _{ON} /I _{OFF} (dB)	R (A/W)	D* (Jones)	I _{ON} /I _{OFF} (dB)	R (A/W)	D* (Jones)	I _{ON} /I _{OFF} (dB)	R (A/W)	D* (Jones)	
MoO ₃ /c-Si heterojunction	63.2	0.41	3.9×10 ¹¹	-	-	-	-	-	-	[31]
Graphene/PdSe ₂ /Ge Heterojunction	20	0.69	1.2×10 ¹³	28	1.72	2 ×10 ¹³	55.9	4.7	7.4×10 ¹³	[32]
SnO ₂ Microwire/Cs PbBr ₃ structure	35	0.03	1.6×10 ¹⁰	35.5	0.46	1.2×10 ¹⁰	-	-	-	[33]
Au NPs/p-ZnO NSs/n-ZnO	61.3	0.73	3.4×10 ¹²	19.7	0.08	5.3×10 ¹¹	-	-	-	[34]
ZnO/Si heterjunction	66.2	0.55	4.8×10 ¹³	-	0.68	5.8×10 ¹³	-	-	-	[35]
Grating CsPbBr ₃ /SnO ₂	61.8	0.22	1.2×10 ¹³	52.4	0.01	4×10 ¹²	53.1	0.086	2×10 ¹²	[36]
Inclined TiO ₂ /Ag/TiO ₂ multilayer	137.2	0.2	5.3×10 ¹³	107.6	0.12	3.5×10 ¹²	-	-	-	[37]
SnS nanostructure	18	0.38	-	16.8	0.49	-	13.8	0.62	-	[38]
ZnO NWs/PbS QDs	59	0.51	3.4×10 ⁸	39	0.07	4.9×10 ⁷	26.8	0.11	4.2×10 ⁷	[39]
Microstructured ZnO/Si	-	0.6	1×10 ¹⁰	-	0.14	-	-	0.06	-	[40]
a-Si based PD	60.6	0.13	4×10 ¹²	/	/	/	/	/	/	This work
a-Si/Ti-based PD	69.1	1.92	9.6×10 ¹²	67.2	1.24	6.2×10 ¹²	58.5	0.93	4.7×10 ¹²	This work

Highlights:

- A new broadband multispectral photodetector based on a-Si/Ti structure is developed.
- Structural, optical and electrical characterizations of the elaborated PD were investigated.
- The proposed multispectral PD exhibits enhanced performances over the conventional sensors.
- The developed photodetector showcases an outstanding performance for Si-photonics technology.

F. Djeffal: Conceptualization, Writing- Reviewing and Editing, Methodology. **N. Boubiche:** elaboration, characterisation. **H. Ferhati:** Writing- Original draft preparation, Software, Validation. **J. Faerber:** characterisation. **F. Le Normand:** characterisation, **N. Javahiraly:** Methodology. **T. Fix:** Methodology

Highly efficient and low-cost multispectral photodetector based on RF sputtered a-Si/Ti multilayer structure for Si-photonics applications

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Abstract

In this paper, a new cost-effective multispectral photodetector (PD) based on amorphous-silicon (a-Si)/titanium (Ti) multilayer structure, which achieves a high UV-Visible-NIR photoresponse is elaborated. A new design strategy based on combining FDTD (Finite Difference Time Domain) with GA (Genetic Algorithm) was used to determinate the a-Si/Ti multilayer geometry providing the highest photoresponsivity in UV, Visible and NIR regions. The optimized structure is then fabricated using RF magnetron sputtering technique. A comprehensive analysis of the photodetector electrical, optical and structural properties was carried out. The sputtered a-Si/Ti multilayer was characterized by Scanning Electron Microscopy (SEM), X-ray diffraction (XRD), and UV-Visible-NIR absorption spectroscopy. The a-Si/Ti multilayer PD exhibits a high broadband absorbance of 80% over the UV and even NIR spectrum ranges [200nm-1100nm]. Moreover, photoelectrical characterization showed that the developed device exhibits an improved responsivity under UV, Visible and NIR lights (1.9 A/W at 365nm, 1.24 A/W at 550 nm and 0.93 A/W at 900 nm) and a high I_{ON}/I_{OFF} ratio of 68 dB. The broadband multispectral photodetection property offered by the proposed a-Si/Ti multilayer PD opens a new route for the fabrication of promising alternative photodetectors for future high-performance and cost-effective optoelectronic systems.

Key words: broadband; RF sputtering; multispectral; photodetector; a-Si/Ti.

1. Introduction

1
2 Optoelectronic systems based on the Silicon-photonics platform are predicted to be the
3
4 most practical technology to meet the cost-effective, large bandwidth, and low power
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6 consumption requirements [1-4]. Photodetector (PD), which is a key component of
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8 optoelectronic communication systems, has received an important research interest due to
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10 their large applications in biomedical imaging, optical wireless communication, light-
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12 detection and robotics [4-8]. Several published works have developed new PD devices, which
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14 can detect different wavelength bands ranging from UV to infrared by using adequate
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16 semiconductor photosensitive materials with appropriate band-gap values [7-10]. Moreover,
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18 the PDs can become more efficient in extensive applications when they are able to detect the
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20 broadband multispectral radiations (UV-Visible-NIR) [10-12]. However, the development of
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22 multispectral and broadband PDs mainly depends on the control and selection of the suitably
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24 matched band-gap materials in order to cover the multispectral range, which is regarded quite
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26 challenging. In this context, combining several semiconductor materials to form
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28 heterostructure that can cover a wide spectral range leads to induce degradation related to
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30 lattice mismatching effects, optical losses and severe recombination effects. These undesired
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32 effects prevent the realization of high-performance broadband photodetectors. Several works
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34 have been proposed to overcome this challenge suggested developing alternative materials
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36 and device structures for broadband multispectral photosensing applications. In this context,
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38 new design methodologies and structures including plasmonic nanoparticles, core-shell
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40 nanostructures, nanowires, metal oxides-based heterojunction and quantum dots have been
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42 developed to achieve high broadband absorbance characteristics [10-20]. Despite the
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44 capability of these designs to provide the broadband multispectral photodetection, they
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46 require costly fabrication techniques and high thermal budget. Additionally, the interface
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48 defects associated with different heterostructure materials can affect the carrier transport
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1 efficiency and light trapping mechanism, thus limiting the sensor photoresponsivity. In this
2 context, researchers have turned out their focus towards the use of 2D-materials and mono-
3 layers in order to overcome these limitations. This is mainly due to their broadband absorption
4 capability, flexibility and high electron mobility [21-23]. Nevertheless, PDs based on 2D-
5 materials reveal a low responsivity due to severe charge recombination effects and its weak
6 absorption behavior. Therefore, the development of novel efficient and low-cost broadband
7 multispectral photodetectors is required to improve the capabilities of optoelectronic
8 technology. Motivated by this concept, the present work aims at developing a new low-cost
9 and highly efficient multispectral photodetector based on RF sputtered a-Si/Ti multilayer
10 structure for Si-phonic applications. To the best of our knowledge, no design techniques
11 based on experiments assisted by numerical optimization using FDTD (Finite Difference
12 Time Domain) and GA (Genetic Algorithm) computations to develop broadband multispectral
13 PDs using a-Si/Ti multilayer structure have been reported. Accordingly, the optimized a-Si/Ti
14 multilayer structure was prepared using RF magnetron sputtering technique. Structural,
15 optical and electrical characterizations of the elaborated a-Si/Ti-based PD were carried out. It
16 is revealed that the developed PD demonstrates outstanding broadband multispectral
17 absorption capabilities over a wide spectrum range with high electrical performances.
18 Moreover, the elaborated photodetector shows high sensitivity values of 1128, 681 and 380
19 over UV, Visible and NIR spectral bands. Therefore, the proposed approach provides a sound
20 pathway for developing broadband sensors based on simple and low-cost structures for high
21 performance Si-photonics applications.

2. Device structure and experimental procedure

22 The development of Broadband multispectral PDs based on a-Si material is extremely
23 difficult. This constraint is mainly due to the intrinsic limited absorption edge of this material.
24 To overcome this absorption limitation, in this work we investigate a new multispectral PD

1 based on non-hydrogenated a-Si dwells on introducing intermediate Ti ultra-thin layers. In
2 this context, Fig.1 (a) illustrates a cross-sectional view of the investigated a-Si/Ti multilayer-
3 based PD device, where highly transparent ITO thin layer is deposited at the top of the
4 structure to reduce the optical reflection losses [4]. The a-Si/Ti multilayer structure is
5 sputtered considered on a glass substrate. As it is shown in this Figure,
6
7 $d_{a-Si} = [d_{Si1}, d_{Si2}, \dots, d_{Sin}]$ and $t_{Ti} = [t_{Ti1}, t_{Ti2}, \dots, t_{Tij}]$ represent the thickness vector values
8 associated with the silicon and titanium layers, respectively. Besides, n and j denote the
9 number of a-Si and Ti sub-layers, respectively. The thickness of the PD device is $t_{a-Si/Ti}$. For
10 the numerical simulation framework, the optical properties (absorbance, reflectance and
11 transmittance) of the investigated PD structure are calculated using FDTD method provided
12 SILVACO software [24].
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27 As far as we are concerned, the development of highly efficient and low-cost
28 multispectral sensors through intuiting the multi-layer structural, geometrical and electrical
29 parameters by using the well-known optical and electrical properties of PDs is not sufficient
30 to achieve the best electrical performances and highest photoresponsivity over a wide
31 spectrum range. Alternatively, we believe that sophisticated numerical optimization strategies
32 behaving like predictive simulations are required to forecast the sensor performance. In this
33 context, the use metaheuristic optimization approaches such as GA technique is a powerful
34 tool for identifying the optimal geometrical configuration of the a-Si/Ti multilayer structure to
35 achieve the highest multispectral photoresponsivity. In this context, modeling and
36 optimization frameworks based on FDTD and GA method are considered in the present work
37 to predict the optical performances of the investigated a-Si/Ti structure. This technique is
38 implemented to selecting the most suitable a-Si/Metal multilayer offering the highest
39 absorbance efficiency over a wide spectrum range. The electrical transport model is not
40 included in the performed predictive simulation. The introduction of the electrical modeling
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combined with FDTD optical modeling in GA-based computation is time consuming due to the use of complex multilayer design with a high number of sub-layers. To do so, Fig.1 (b) shows the flowchart of the adopted hybrid design approach based on combined GA and numerical simulation techniques. The optical device properties are simulated using 2D-FDTD method. More details regarding the suggested modeling approach can be found in our previously published works [25-27].

The simulated spectral absorbance using FDTD technique is explored to formulate the objective (fitness) function, which will be minimized using GA-based optimization method. The fitness function is given by the following formula

$$Fitness (X_i) = \left(\frac{1}{A[\lambda_{\min}, \lambda_{\max}]} \right) \quad (1)$$

where A represents the average absorbance over the spectral range of $[\lambda_{\min}, \lambda_{\max}]$ with $\lambda_{\min} = 200nm$ and $\lambda_{\max} = 1100nm$ are respectively the minimum and the maximum wavelength values considered for broadband photosensing of PDs, X_i denotes the design parameter vector.

Various metals (Ag, Au, Ni and Ti) are introduced in the optimization procedure. After carrying out the optimization procedure, the resulted design parameter vector of the investigated a-Si/Ti multilayer active-film is given by

$$X_i = (d_{a-Si} = [20nm, 36nm, 50nm, 40nm], t_{ITO} = 20nm, t_{Ti} = [9nm, 8nm, 7nm], j = 3).$$

Fig.1 (c) shows the absorbance spectrum of the optimized a-Si/Ti structure. While the optimized metal is the Titanium, the optimized PD structure reveals a very high average absorbance of 81.3% over UV-Vis-NIR spectral range, indicating its broadband sensing properties. This makes it a promising candidate for elaborating highly efficient and low-cost multispectral photodetectors. This enhancement is attributed to the role of GA-based optimization tool in selecting the appropriate multilayer structure through promoting enhanced light-scattering

1 effects. The obtained design will be used to elaborate the optimized a-Si/Ti multilayer sensor,
2 which is the main objective of the next part.
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4 The proposed structure can be elaborated at deposition temperatures of 300 K, where the
5 optimized a-Si/Ti multilayer is suggested on glass substrate. This is considered as a major
6 advantage for the development of low-cost broadband photodetectors. In fact, the proposed
7 structure can be prepared on Silicon substrate. However, the use of Silicon platform based on
8 CMOS technology can impose the high thermal budget process and can also affect the device
9 optical properties [28]. On the other hand, the use of back-end-of-line (BEOL) requires a
10 complex structure involving contacts, insulating layers (dielectrics), metal levels, and bonding
11 sites for chip-to-package connections. This can in turn affect the device optical behavior and
12 the multispectral photodetection ability. Thus, these challenges should be taken into account
13 for the realization of multispectral photodetectors compatible with the state-of-the-art CMOS
14 technology. On the other hand, from an application perspective, it is important to note that the
15 proposed a-Si/Ti multilayer can be developed on flexible substrates.
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33 The elaboration of the optimized PD is based on three-step manufacturing processes. In
34 the beginning, glass substrates were ultrasonically cleaned up using an ultrasonic bath and
35 commercial detergent and then dried under a nitrogen jet procedure. Afterwards, successive
36 deposition of the optimized a-Si and Ti thin-films on the glass substrate was carried out using
37 *RF* magnetron sputtering technique (MOORFIELD MiniLab 060). To do so, p-type Si and Ti
38 targets with high purity of 99.99% were used. This experimental technique is commonly used
39 to elaborate high-quality thin-layers [29-31]. The sputtering process of a-Si and Ti sub-layers
40 was performed in a pure *Ar* atmosphere with a pressure of 1.5 Pa. The deposition parameters
41 were carefully tuned in order to obtain unhydrogenated a-Si state, Besides, the targets to
42 substrate distances were kept at 6.5 cm and 5.1 cm for the Titanium and Si materials,
43 respectively. The sputtering deposition parameters for all sub-layers are summarized in
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Table.1. The ITO ultrathin film was deposited on the sputtered a-Si/Ti multilayer by using targets with 90 wt% In₂O₃ and 10 wt% SnO₂. The sputtering process for ITO thin-film was carried out in a mixture atmosphere of Ar and O₂ (Ar: 66%, O₂: 33%), where high-purity argon (99.99%) and oxygen (99.99%) gases are used. It is worthy to note that the RF sputter was calibrated before the deposition of deferent thin films, where each layer was separately grown on glass substrates to select the appropriate deposition parameters.

In order to assess the optoelectronic performances of the fabricated sensor, structural and optical characterizations were conducted using X-ray diffraction measurements (ARL Equinox 3000) for 2θ diffraction angle scans of [25°-80°] and UV-Visible-NIR spectrophotometer (F10-RT-UV). The morphological characteristics of the prepared sample were analyzed using scanning electron microscopy (SEM), where the surface (top) was imaged with a Zeiss Gemini SEM 500 with a field emission Schottky source. The semiconductor characterization system (Keithley 4200-SCS) was employed to measure the current-voltage characteristics of the prepared device under dark and illumination conditions.

3. Results and discussions

The aim of this work is to investigate the role of introducing a-Si/Ti multilayered structure with optimized geometry in improving the photosensing performances of PDs over a wide spectral range. The structural properties of the prepared sample based on embedded a-Si and Ti sputter-deposited thin-films are investigated using XRD technique. In this context, Fig.2 (a) shows XRD measurements for (2θ) diffraction angle scanning from 25° to 80° of the prepared samples based on ITO/a-Si thin-film and a-Si/Ti multilayered structure. The XRD pattern of the elaborated sample with ITO/a-Si shows a low-intensity XRD peak indexed to the (222) crystal plane of the ITO material. It can be also seen from this spectra the presence of a diffraction peak at 28.5° angle, corresponding the (111) facets of silicon. This indicates that the sputtering of thick Si films (t_{a-Si}=130 nm) enables the formation of Si microcrystals.

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However, it can be noticed from the XRD pattern of the elaborated a-Si/Ti multilayer structure depicted in Fig.2 (a), the amorphous state of the silicon and ITO sputtered layers, where no coherent XRD peaks are matching these materials. The obtained crystalline characteristics can be explained by the ultralow thickness of the deposited silicon sub-layers, which can prevent reaching the crystallization phase of the Si material. On the other hand, this pattern demonstrates the presence of crystallized Ti metal, manifesting (101)-oriented film at the diffraction angle of 39.5° . This highlights the beginning of the crystallization phase of the deposited Ti inter-layers. Fig.2 (b) shows the SEM top surface image of the fabricated ITO/a-Si/Ti multilayered sample. It can be seen from this micrograph that granulated ITO surface with roughness characteristics is observed. This indicates that the growth is essentially columnar for the embedded a-Si and Ti sub-layers, which further explains the obtained amorphous state of the sputtered silicon thin-films as it is shown in Fig.2 (a). In other words, as the a-Si and Ti thin-films are embedded by RF sputtering technique, the structure roughness significantly increases and when the grain size is superior to the film thickness, the growth becomes columnar particularly for the deposited layers closest to the surface.

One of the most important criteria that active layers of multispectral PDs should satisfy is to offer a broadband absorption property. To assess the absorption capabilities of the prepared sample based on stacked a-Si and Ti sub-layers with optimized geometry, the absorbance spectra of the elaborated samples were extracted and illustrated in Fig.3. It can be observed from this figure that significant changes concerning the optical behavior of the PD active film are achieved by inserting an optimized a-Si/Ti multilayer. It demonstrates highly improved absorption efficiency exceeding 85% over UV-Vis-NIR spectral range as compared to that of a-Si thin-film (28.2%). This yields a high relative enhancement of 183%. This achievement is due to the effectiveness of the introduced FDTD-GA hybrid approach in promoting enhanced light trapping capabilities of embedded a-Si and Ti sub-layers with suitable geometry. In other

1 words, the introduction of Ti intermediate metal films within the a-Si layer can generate
2 optical micro-cavities, which leads to extend the optical path in the PD active layer thereby
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4 resulting in a broadband absorption characteristic. On the other hand, it can be observed from
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6 Fig.3 that the obtained experimental results are found in a good agreement with the theoretical
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8 ones, where only small discrepancies between both experimental and numerical data are
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10 observed over the UV spectral range. This can be attributed to the experimental condition, the
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12 prepared structure shows surface roughness and the growth is columnar particularly for the
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14 top sub-layers as it is shown in Fig.2. This unexpected effect has also contributed to further
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16 enhancing the multilayer light trapping capability due to the development of nanostructured
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18 columnar for the sputtered sub-layers closest to the surface. In this context, effects related to
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20 experimental conditions such as the resulted columnar structure are not included in the
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22 performed simulations. This explains the above-mentioned discrepancies concerning the
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24 obtained absorbance spectra from simulation and experimental data. To achieve a close
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26 resemblance between the numerical and experimental data, several experimental parameters
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28 of the sputtering technique should be taken into account, which is considered extremely
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30 difficult. Therefore, the fabrication of such an optimized a-Si/Ti multilayered structure as an
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32 MSM photodetector can extend the light harvesting capability into the visible and NIR
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34 spectral ranges, making it very promising candidate for the development of high-responsivity
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36 broadband PDs at low-cost.
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47 To further investigate the multispectral photoresponse of the prepared PD based on
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49 stacked a-Si and Ti thin-films, the sample is realized as an MSM photodetector. In this
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51 framework, top and bottom gold contacts were evaporated via E-beam evaporation technique
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53 as it is shown in Fig.1 (a). The fabricated device was then illuminated by monochromatic light
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55 signals with wavelength values of 365 nm, 550 nm and 900 nm using LED lamps. **Moreover,**
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57 **to show the capability of the proposed experiment assisted by FDTD-GA hybrid approach in**
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developing broadband PDs based on simple and low-cost structures, the device sensitivity and responsivity are estimated using the following formulas

$$S = \frac{I_{ph} - I_{dark}}{I_{dark}} \times 100 \quad (1)$$

$$R = \frac{I_{ph}}{P_i} \text{ [A/W]} \quad (2)$$

where I_{ph} and I_{dark} represent the measured currents under illumination and dark conditions, P_i denotes the optical power density.

The measured I-V characteristics in darkness and under illumination conditions of the prepared sensors based on a-Si and a-Si/Ti multilayer active films are depicted in Fig.4 (a) and (b) respectively. It can be seen from Fig.4 (a) that the a-Si based PD shows a good photoresponse only in the UV range. On the other hand, Fig.4 (b) demonstrates the ability of the prepared PD with embedded a-Si and Ti sub-layers for providing multispectral photodetection capability. The device shows excellent sensing properties with high photocurrent values of 0.68 mA, 0.22 mA and 0.1 mA under UV, visible and NIR lights, respectively at an applied voltage of 3V. Moreover, the elaborated photodetector shows high sensitivity values of 1128, 681 and 380 over UV, Visible and NIR spectral bands. Such finding correlates well with the above-outlined broadband absorption characteristic of the optimized structure based on embedded a-Si and Ti thin-films. Basically, the latter structure shows an extended absorption to the visible and NIR regions, which can enables enhancing the carrier generation mechanism. This effect leads to achieve an improved broadband photoresponse. More importantly, the use of stacked a-Si and Ti layers can enlarge the depletion layer in the active layer due to the Schottky nature of the a-Si/Ti contact. This can in turn improve the separation mechanism of the photo-excited e/h pairs, thus reducing recombination losses. The self-powered property, which describes the ability of device to operate without the need of any applied voltage ($V_{input}=0V$) is highly required for developing

1 high-performance and low-power consumption photodetectors. It seems important to assess
2 the ability of the prepared photodetector to offer the self-powered characteristic. In this
3 context, it can be observed from Fig.4 (b) that the proposed PD based on a-Si/Ti multilayer
4 provides a favorable photocurrent at zero bias condition, where the measured I-V curves are
5 shifted to negative voltages. This phenomenon is attributed to the degraded homogeneity of
6 the deposited sub-layers, where the sputtering of a-Si and Ti layers closest to the surface is
7 principally columnar as it is above-outlined. In other words, this effect can affect the
8 homogeneity of both contacts, which leads to an asymmetrical electrical behavior as it is
9 shown in Fig.4 (b).
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21 On the other hand, Fig.4 (a) and (b) show that the prepared a-Si/Ti multilayer device
22 exhibits a high current as compared to that of the conventional device in darkness. This is
23 mainly due to the improved conductivity of the device, where introducing Ti metal layer
24 induces significant changes in the device resistive behavior. This can lead to reduce the device
25 series resistance and increase the dark current. To consolidate this explanation, the series
26 resistance values of the prepared devices based on a-Si/Ti multilayer and a-Si thin-film are
27 extracted using the electrical characterization methodology provided in our previous work
28 [31]. The results show that the elaborated a-Si/Ti multilayer structure exhibits lower series
29 resistance of $8 \times 10^3 \Omega$ as compared to that of the conventional a-Si-based device ($2 \times 10^4 \Omega$).
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43 Fig.5 depicts the measured spectral responsivity of the elaborated samples based on a-Si
44 thin-film and stacked a-Si and Ti layers. Clearly, the proposed sensor demonstrates a high
45 responsivity over a large spectral band from UV to NIR as compared to the conventional
46 device. The prepared PD with a-Si/Ti multilayered active film exhibits superior responsivity
47 values of 1.9 A/W, 1.24 A/W and 93 mA/W under UV, visible and NIR illumination
48 conditions, respectively. The enhanced multispectral photoresponse characteristics are mainly
49 attributed to the role of the optimized a-Si/Ti multilayer in achieving the dual benefits of
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1 enhanced photogeneration and collection mechanisms. In other words, the introduced FDTD-
2 GA hybrid approach enables selecting the optimized a-Si/Ti multilayer structure offering the
3 highest and broadband absorption. This leads to enhance the quantity of photo-induced
4 carriers and thereby the device responsivity. On the other hand, a-Si/Ti electronic interface
5 exhibits a Schottky behavior leading to induce localized depletion regions. This would reduce
6 the recombination effects thus enhancing the device collection efficiency. Therefore, the
7 combination of these benefits has allowed developing high-performance multispectral
8 photodetector based on cost-effective structure, which can be prepared in room temperature
9 conditions.

10
11 To show the strength of the prepared multispectral PD based on a simple and low-cost
12 embedded a-Si and Ti thin-films as compared to recently developed ones, a comparative
13 performance analysis is carried out. Accordingly, the associated FoM parameters including
14 current ratio (I_{ON}/I_{OFF} ratio), responsivity and detectivity are extracted and summarized in
15 Table.2. This table confirms the ability of the optimized structure for outperforming other
16 perovskite, silicon and nanostructured multispectral PD structures in terms of FoM parameters
17 [32-41]. Although some reported devices demonstrated superior visible photoresponse, they
18 either exhibited a compromised UV sensitivity, stability issues and/or required the use of
19 critical raw materials and processing complexity. Alternatively, the present PD with stacked a-
20 Si and Ti thin-films provides a new strategy for achieving high and broadband photosensing
21 characteristics at low manufacturing cost. These results clearly demonstrate the great potential
22 of the proposed a-Si/Ti multilayer structure for multispectral photodetection application.

23 **4. Conclusion**

24 In this work, we have developed a new high-photoresponsivity multispectral PD based on
25 ITO/a-Si multilayer structure. The numerical simulation and optimization of the structure using
26 combined FDTD-GA approach offer improved photoresponsivity and broadband absorption
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1 capabilities. The optimized design was employed in fabricating multispectral photodetector
2 using RF magnetron sputtering technique. The device structural and optical properties were
3 investigated using XRD and UV-Vis-NIR spectroscopy methods. It was found that excellent
4 UV-Vis-NIR absorbance with over than 80% average value was recorded which can lead to
5 improve the device photoresponsivity. In this context, the elaborated sensor offers ultra-high
6 responsivity values of 1.9 A/W, 1.24A/W and 0.93 A/W under UV, visible and NIR
7 illumination, respectively. This multispectral photodetection property is mainly attributed to
8 the effective light-management provided by the optimized design. Moreover, it is
9 demonstrated that the elaborated PD based on embedded a-Si and Ti sub-layers can operate in
10 self-powered mode, showing a favorable photocurrent of 0.4 μ A. The proposed elaboration
11 methodology can contribute in a fascinating breakthrough towards broadband multispectral
12 photodetector devices based on Si-photonics platform.
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Figures caption:

Fig.1 (a): Device structure with MSM Schottky PD configuration based on the proposed a-Si/Ti multilayer structure. **(b)** Flowchart of the adopted hybrid design approach based on combined GA and numerical simulation techniques. **(c)** Absorbance spectrum of the optimized a-Si/Ti multilayered structure.

Fig.2 (a) X-ray diffraction patterns of the elaborated a-Si/Ti structure with $t_{\text{a-Si/Ti}}=170\text{nm}$ and $t_{\text{ITO}}=20\text{nm}$. **(b)** SEM images of top surface of the elaborated a-Si/Ti multilayer structure using RF magnetron sputtering technique.

Fig.3: Absorbance spectra of the prepared ITO/a-Si and a-Si/Ti multilayer samples with $t_{\text{a-Si/Ti}}=170\text{nm}$ and $t_{\text{ITO}}=20\text{nm}$.

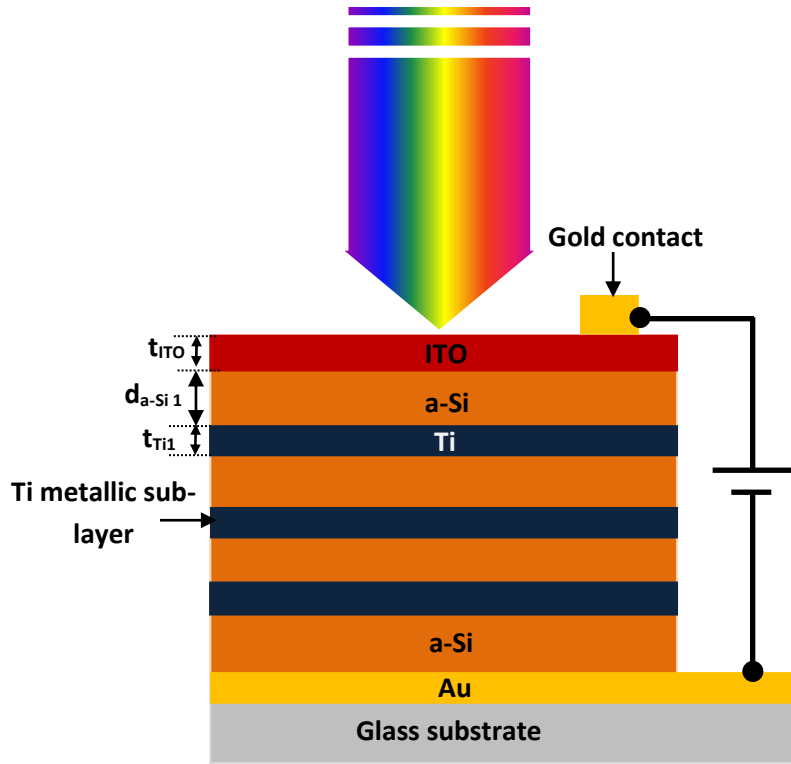
Fig.4: Measured I-V characteristics under dark and light-exposure conditions in UV, visible and NIR spectrum bands of **(a)** the conventional device with a-Si active layer, **(b)** the prepared PD based on embedded a-Si and Ti sub-layers.

Fig.5: Spectral photoresponsivity of the prepared PD structures based on a-Si thin-film and a-Si/Ti multilayer.

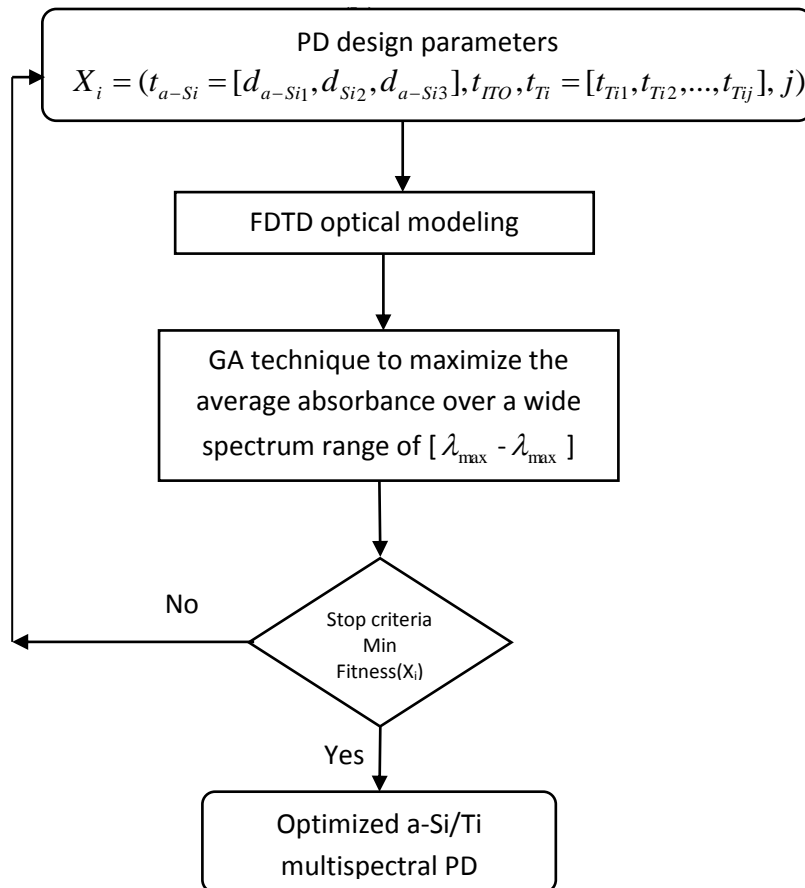
Tables:

Table.1: Deposition parameters of the sputtered ITO/a-Si/Ti multilayer structure.

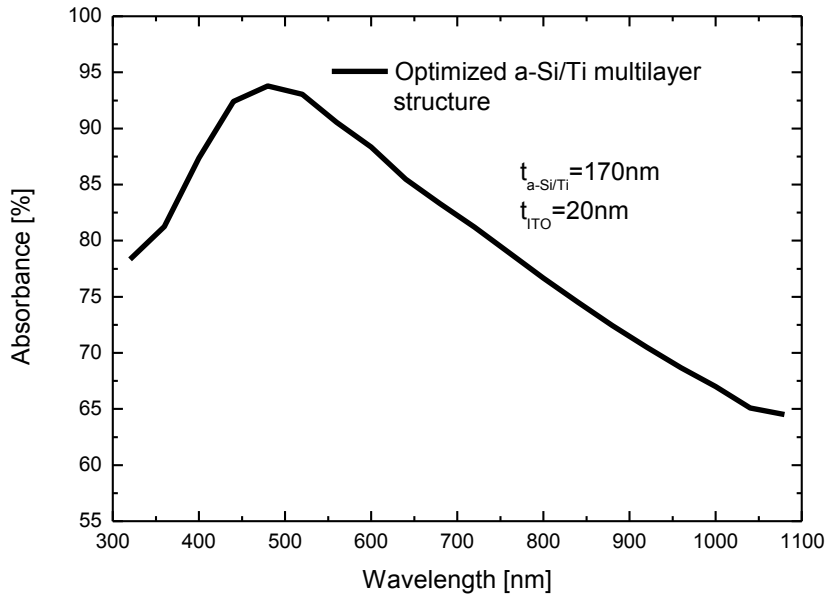
Table.2: Overall performance comparison between the elaborated PD and several reported multispectral photodetector devices.



(a)



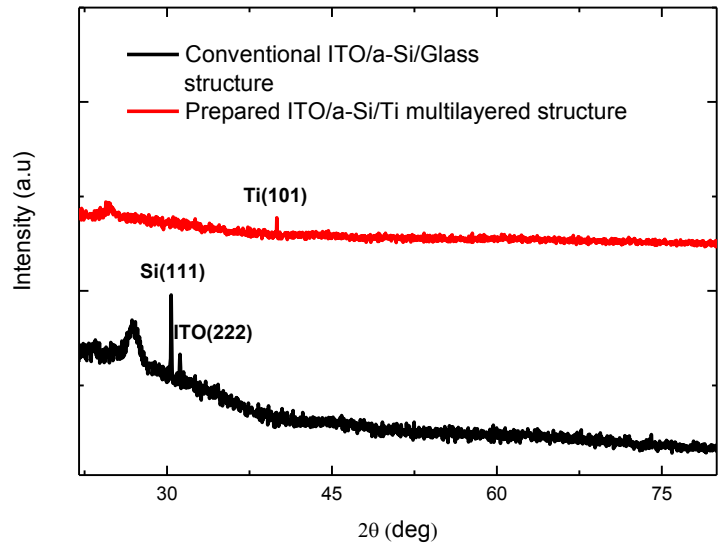
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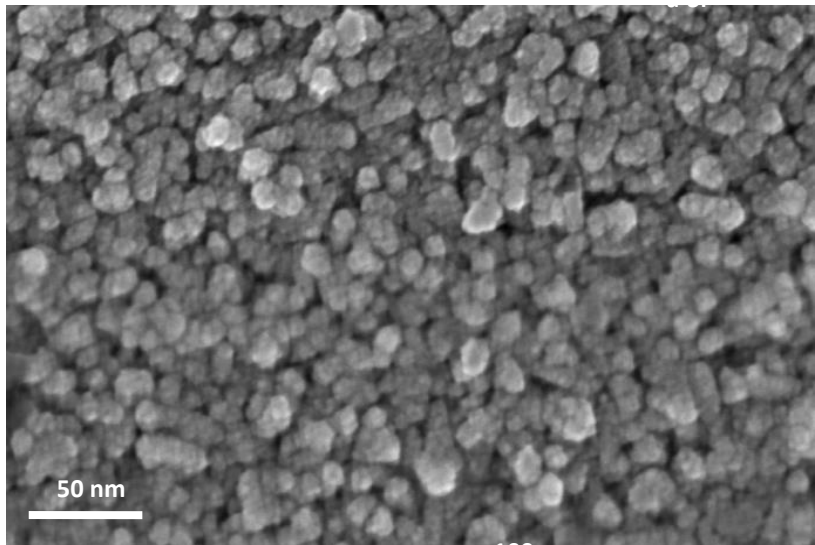
(c)

Figure.1

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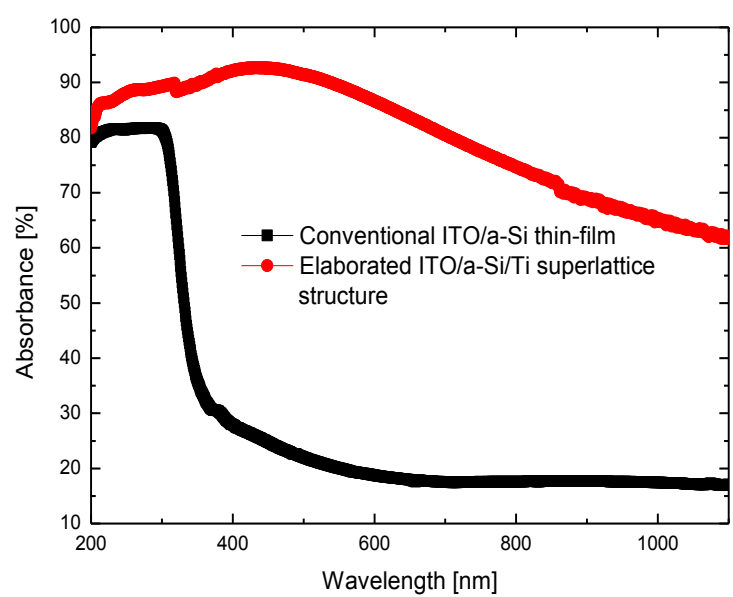
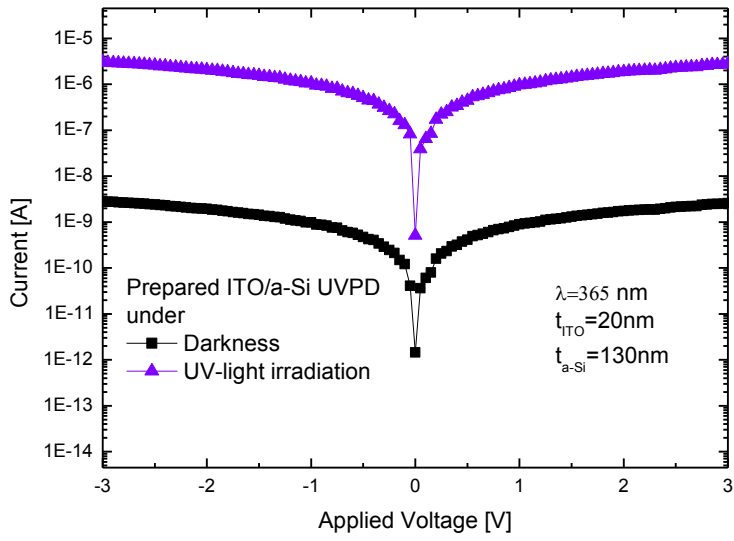
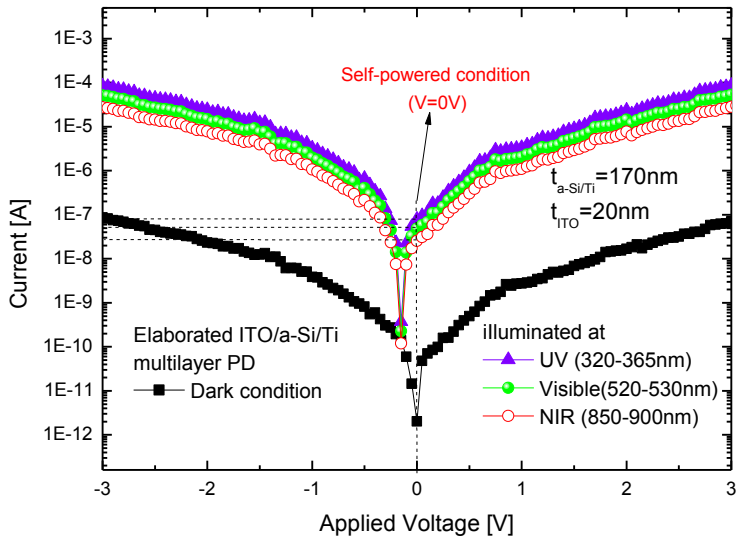


Figure.3



(a)



(b)

Figure.4

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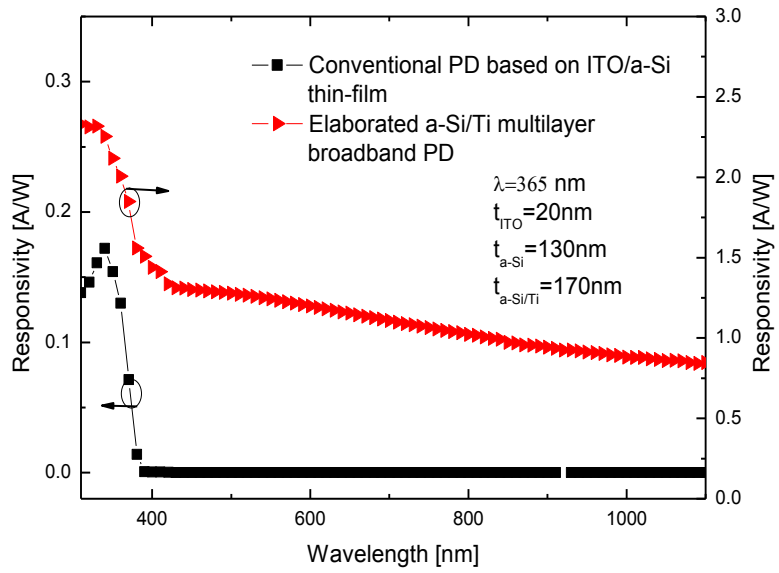


Figure.5

Table.1

Parameter	ITO	a-Si	Ti
Target	(90% In ₂ O ₃ ,10% SnO ₂)	99.99% p-Si	99.99% Ti
Target to substrate distance (cm)	5	5.1	6.5
Gas composition (Ar: O ₂)	(66%: 33%)	/	/
Substrate temperature (K)	300	300	300
power of <i>RF</i> source (W)	240	250	250
Working pressure (Pa)	1.5	1.5	1.5
deposition rate (nm/s)	0.2	0.4	0.7

Table.2

UV-Vis-NIR PD structures	UV (320-365 nm)			Visible (green) (515-525 nm)			NIR (880-900 nm)			Ref.
	I _{ON} /I _{OFF} (dB)	R (A/W)	D* (Jones)	I _{ON} /I _{OFF} (dB)	R (A/W)	D* (Jones)	I _{ON} /I _{OFF} (dB)	R (A/W)	D* (Jones)	
MoO ₃ /c-Si heterojunction	63.2	0.41	3.9×10 ¹¹	-	-	-	-	-	-	[32]
Graphene/PdSe ₂ /Ge Heterojunction	20	0.69	1.2×10 ¹³	28	1.72	2 ×10 ¹³	55.9	4.7	7.4×10 ¹³	[33]
SnO ₂ Microwire/Cs PbBr ₃ structure	35	0.03	1.6×10 ¹⁰	35.5	0.46	1.2×10 ¹⁰	-	-	-	[34]
Au NPs/p-ZnO NSs/n-ZnO	61.3	0.73	3.4×10 ¹²	19.7	0.08	5.3×10 ¹¹	-	-	-	[35]
ZnO/Si heterjunction	66.2	0.55	4.8×10 ¹³	-	0.68	5.8×10 ¹³	-	-	-	[36]
Grating CsPbBr ₃ /SnO ₂	61.8	0.22	1.2×10 ¹³	52.4	0.01	4×10 ¹²	53.1	0.086	2×10 ¹²	[37]
Inclined TiO ₂ /Ag/TiO ₂ multilayer	137.2	0.2	5.3×10 ¹³	107.6	0.12	3.5×10 ¹²	-	-	-	[38]
SnS nanostructure	18	0.38	-	16.8	0.49	-	13.8	0.62	-	[39]
ZnO NWs/PbS QDs	59	0.51	3.4×10 ⁸	39	0.07	4.9×10 ⁷	26.8	0.11	4.2×10 ⁷	[40]
Microstructured ZnO/Si	-	0.6	1×10 ¹⁰	-	0.14	-	-	0.06	-	[41]
a-Si based PD	60.6	0.13	4×10 ¹²	/	/	/	/	/	/	This work
Optimized a-Si/Ti structure	69.1	1.92	9.6×10 ¹²	67.2	1.24	6.2×10 ¹²	58.5	0.93	4.7×10 ¹²	This work